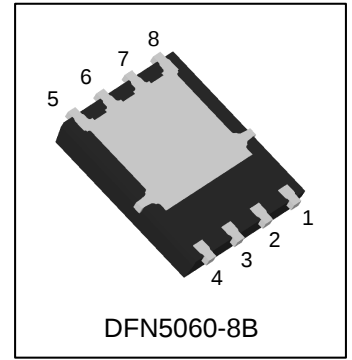


LN70065DT3WG

250V N-Channel Power MOSFET

1. FEATURES

- Low thermal impedance.
- Fast switching speed.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

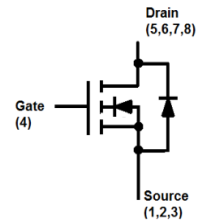


2. APPLICATIONS

- Power Tools
- UPS
- Motor Control

3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
LN70065DT3WG	LN70065	5000/Tape&Reel



4. MAXIMUM RATINGS

Parameter		Symbol	Limits	Unit
Drain-to-Source Voltage		VDS	250	V
Gate-to-Source Voltage		VGS	± 20	V
Continuous Drain Current(Note 1)	TA =25°C	ID	5	A
	TA =100°C	ID	3	
Pulsed Drain Current(Note 2)	TA =25°C	IDM	20	
Continuous Drain Current	TC =25°C	ID	21	A
	TC =100°C	ID	14	
Pulsed Drain Current	TC =25°C	IDM	84	
Avalanche Current		IAS	13	A
Avalanche energy(L=0.1mH)		EAS	8.5	mJ
Power Dissipation(Note 1)	TA =25°C	PD	2.2	W
	TA =100°C		0.9	
Power Dissipation	TC =25°C		62.5	
	TC =100°C		25	
Operating Junction and Storage Temperature Range		TJ , TSTG	-55~+150	°C

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Junction-to-Ambient(Note 1)	RθJA	55	°C/W
Junction-to-Case	RθJC	2	

Note:1.Surface mounted on "1.5in x 1.5in" FR4 board using 1*1 in pad, 2 oz Cu.

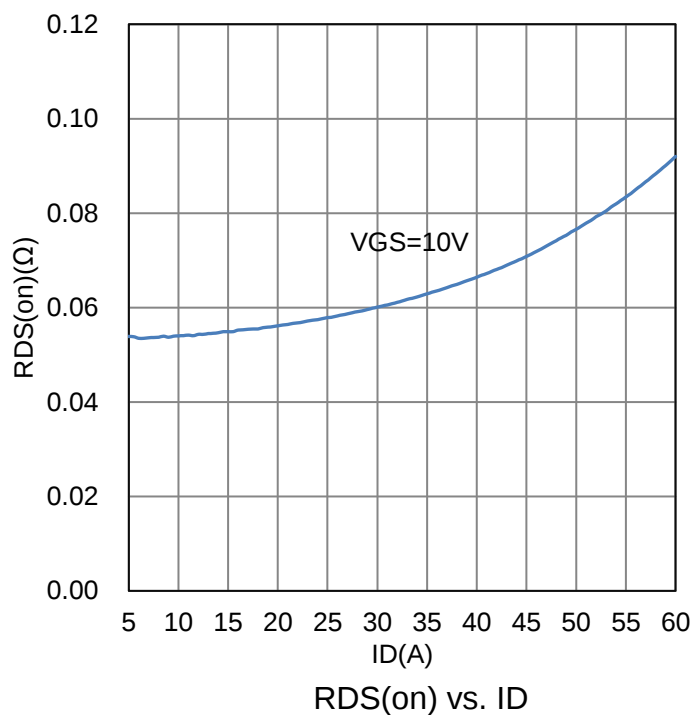
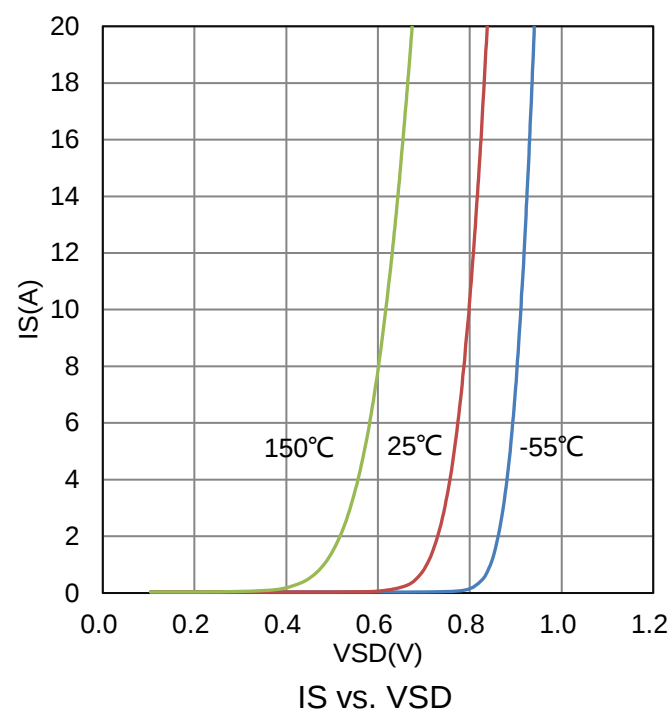
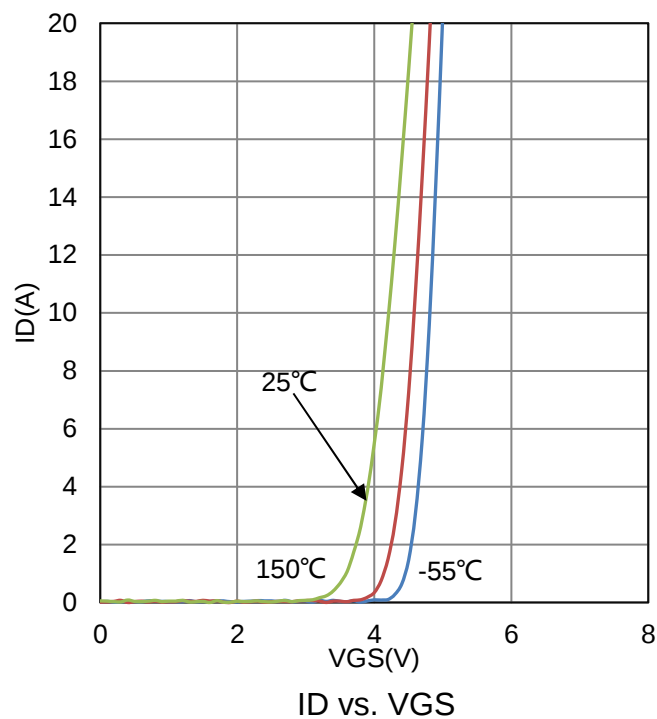
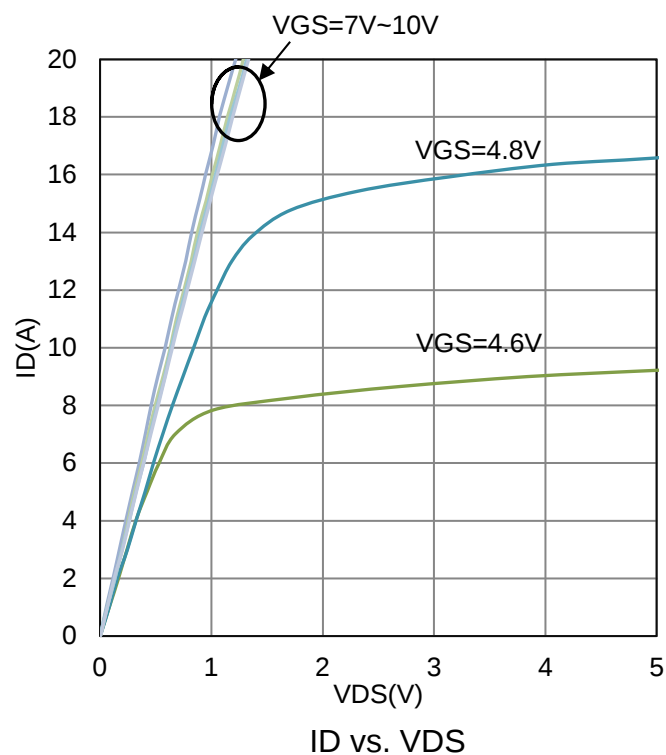
2.Pulse width limited by maximum junction temperature.

6. ELECTRICAL CHARACTERISTICS

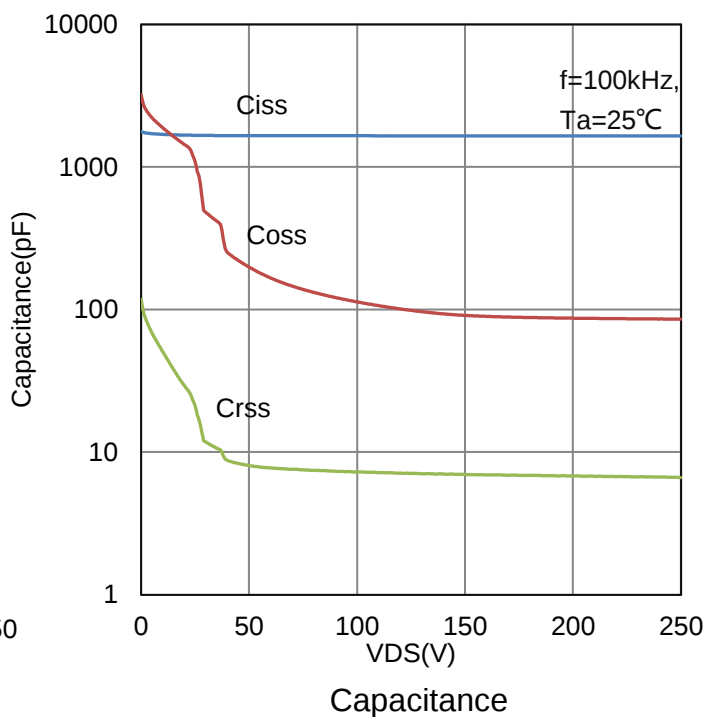
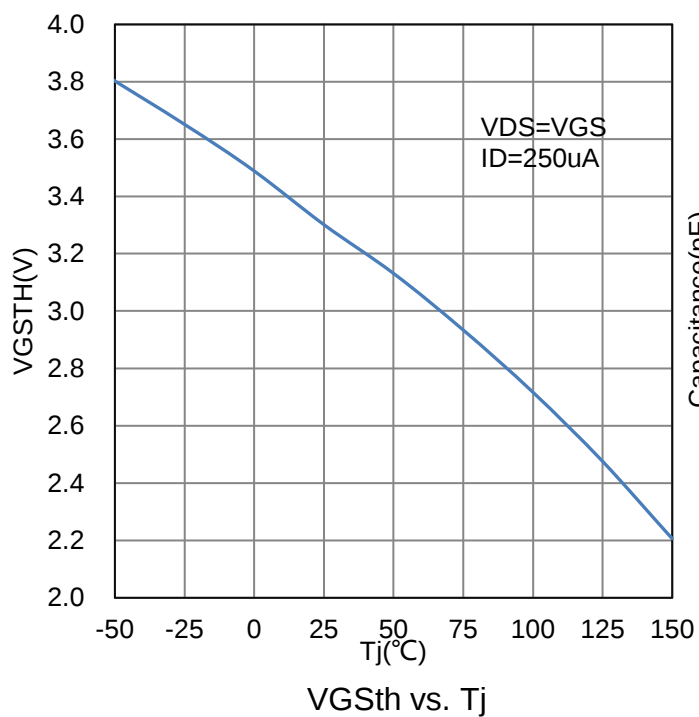
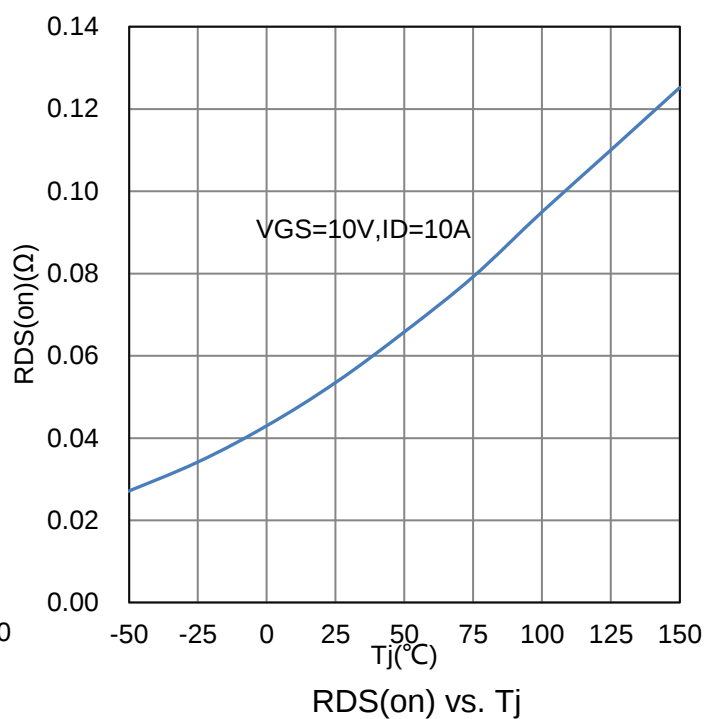
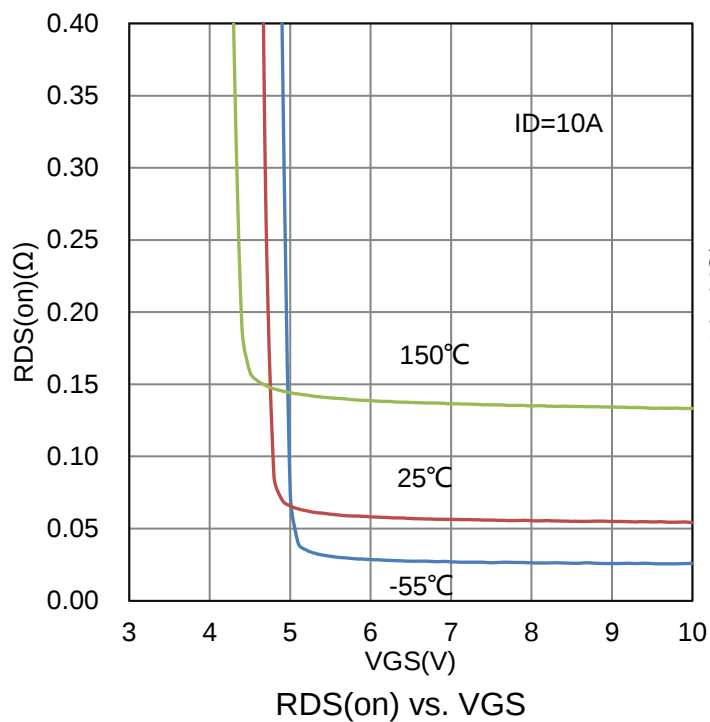
Characteristic		Symbol	Min.	Typ.	Max.	Unit
Static						
Drain to Source Breakdown Voltage (VGS = 0 V, ID = 250 μA)		BVDSS	250	-	-	V
Gate-Source Threshold Voltage (VDS = VGS , ID = 250 uA)		VGS(th)	2	3	4	V
Gate-Body Leakage (VDS = 0 V, VGS = ±20 V)		IGSS	-	-	±100	nA
Zero Gate Voltage Drain Current (VDS = 250 V, VGS = 0 V)		IDSS	-	-	1	μA
Drain-Source On-Resistance(Note 3) (VGS = 10 V, ID = 10 A)		RDS(on)	-	50	65	mΩ
Dynamic						
Input Capacitance	(VDS = 125 V, VGS = 0 V, f = 100KHz)	Ciss	-	1740	-	pF
Output Capacitance		Coss	-	104	-	
Reverse Transfer Capacitance		Crss	-	7.6	-	
Total Gate Charge	(VDS = 125 V, VGS = 10 V, ID = 10 A)	Qg	-	20	-	nC
Gate-Source Charge		Qgs	-	7.5	-	
Gate-Drain Charge		Qgd	-	3	-	
Turn-On Delay Time	(VDS = 125 V, ID = 10 A, VGS = 10 V, RG = 10 Ω)	td(on)	-	20	-	ns
Rise Time		tr	-	19	-	
Turn-Off Delay Time		td(off)	-	46	-	
Fall Time		tf	-	16	-	
Diode characteristics						
Continuous Current TC =25° C		IS	-	-	21	A
Plused Current TC =25° C		ISM	-	-	84	A
Diode Forward Voltage (IS = 20 A,VGS = 0 V)		VSD	-	0.9	1.3	V
Reverse Recovery Time (VR=125V,IF=10A,dIF/dt=100A/us)		trr	-	125	-	ns
Reverse Recovery Charge (VR=125V,IF=10A,dIF/dt=100A/us)		Qrr	-	620	-	nC
Reverse Recovery Current (VR=125V,IF=10A,dIF/dt=100A/us)		IRRM	-	4.05	-	A

3.Pulse test: PW $\leq$ 300us duty cycle $\leq$ 2%.

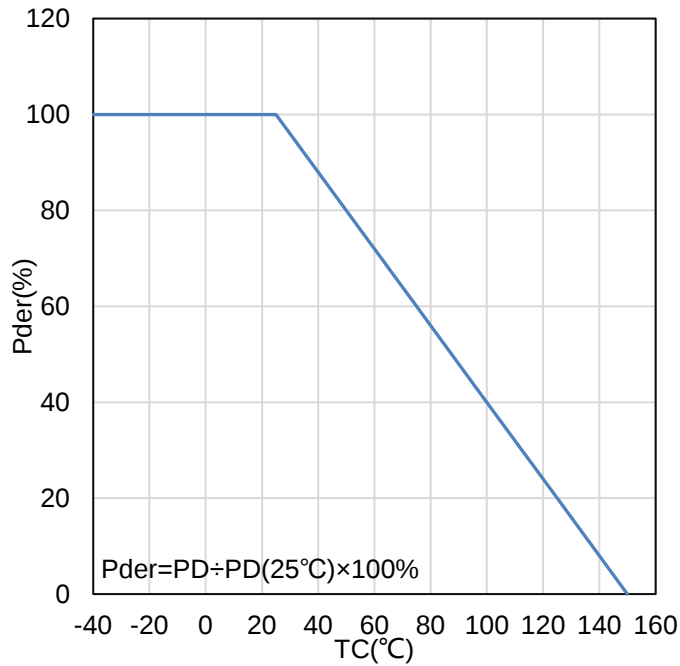
7. ELECTRICAL CHARACTERISTICS CURVES



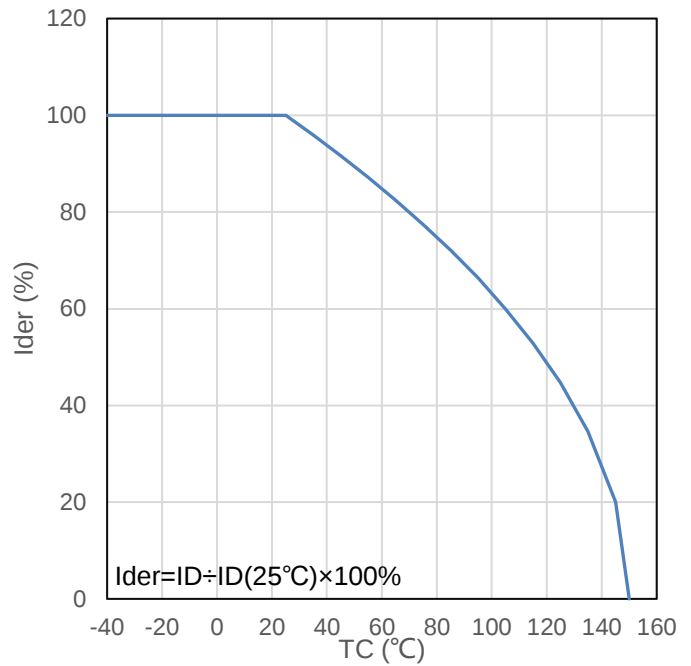
7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



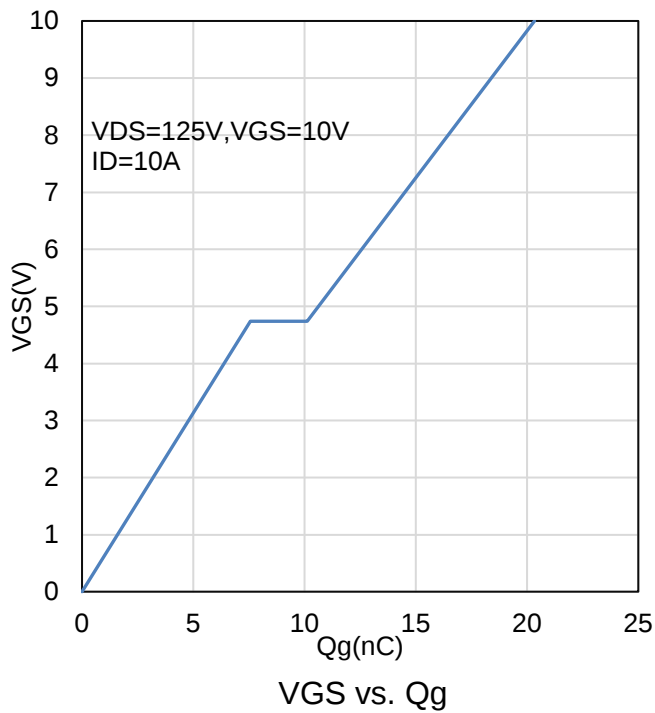
7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



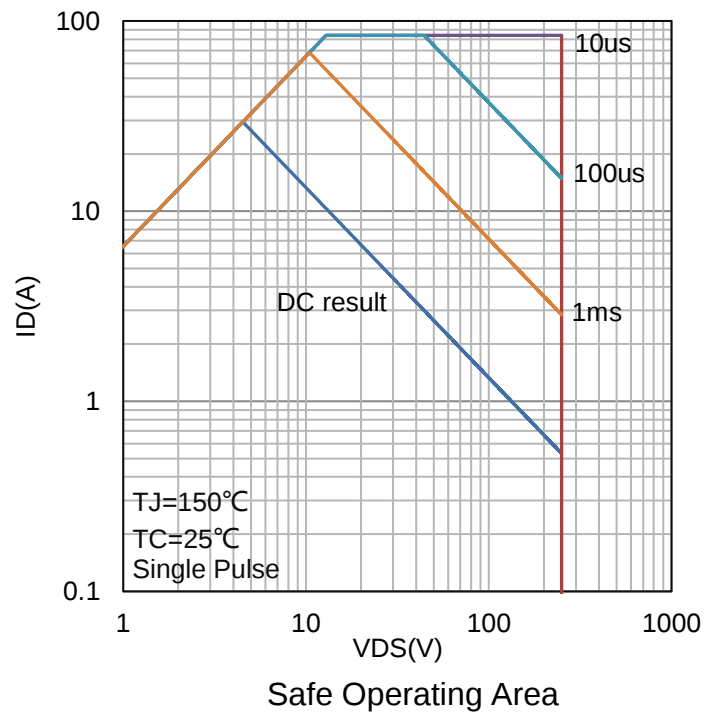
Normalized Derating Curve



Normalized drain Current

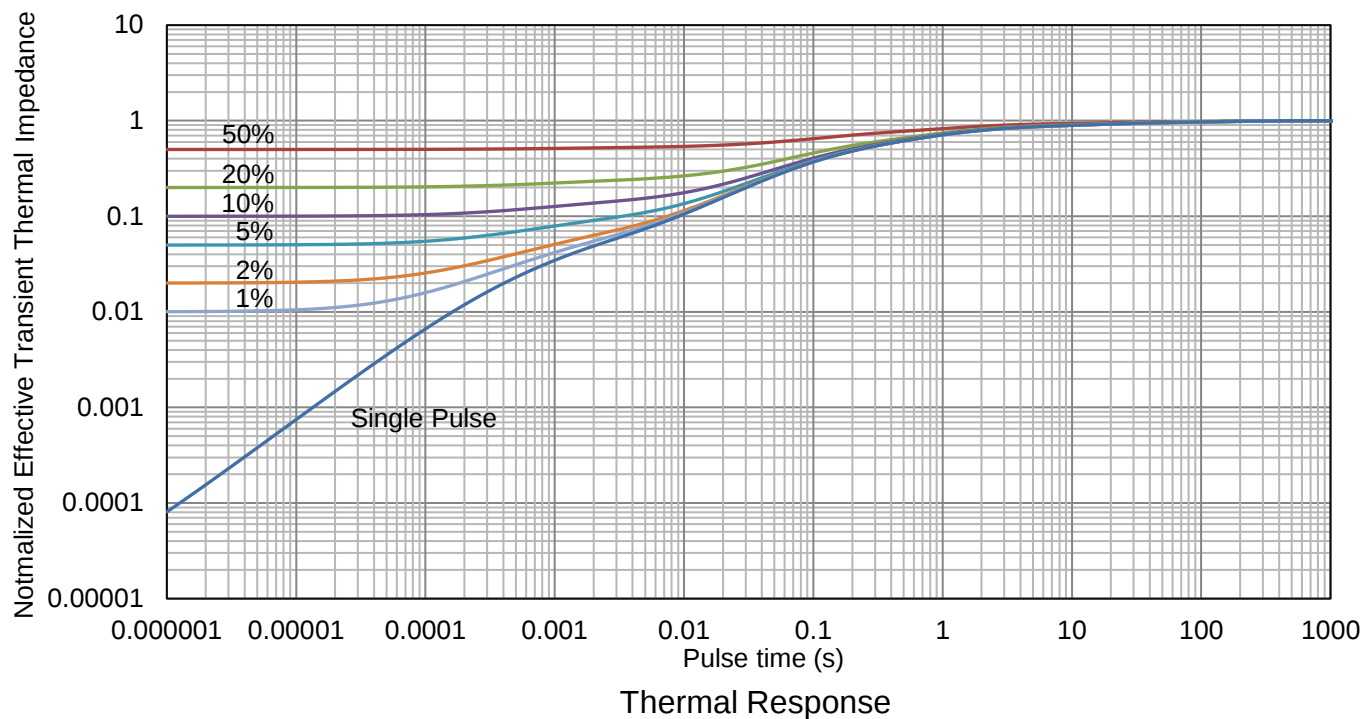


VGS vs. Qg



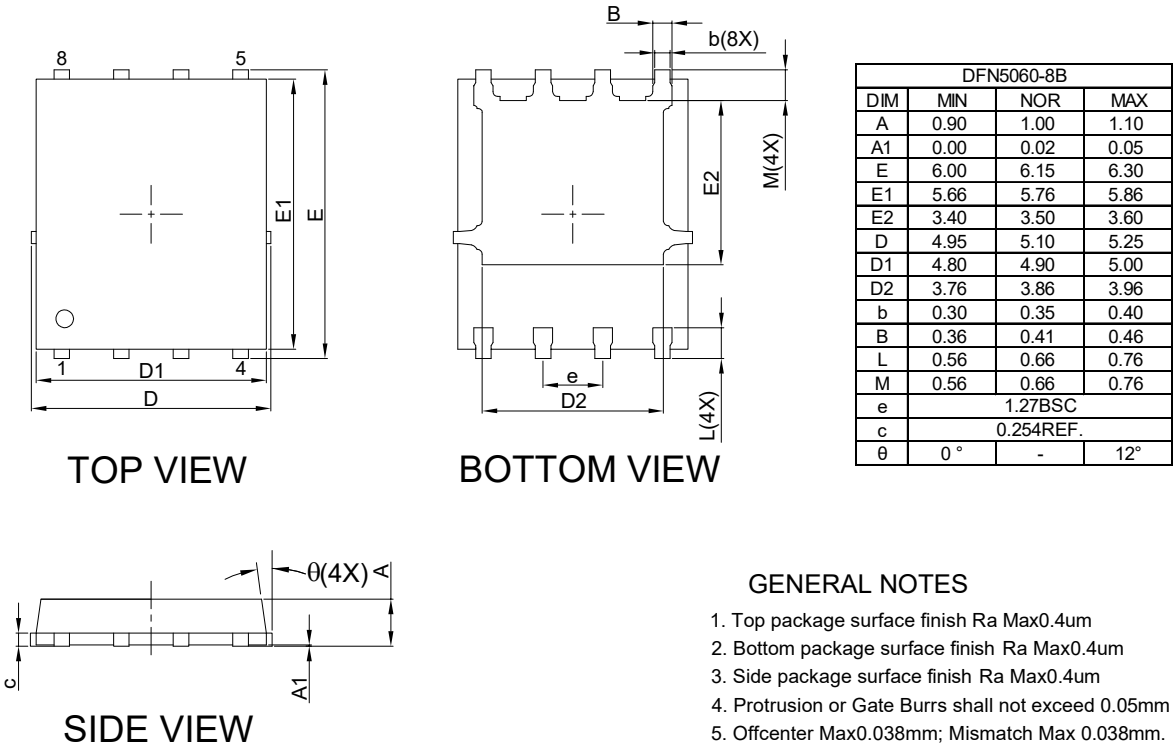
Safe Operating Area

7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

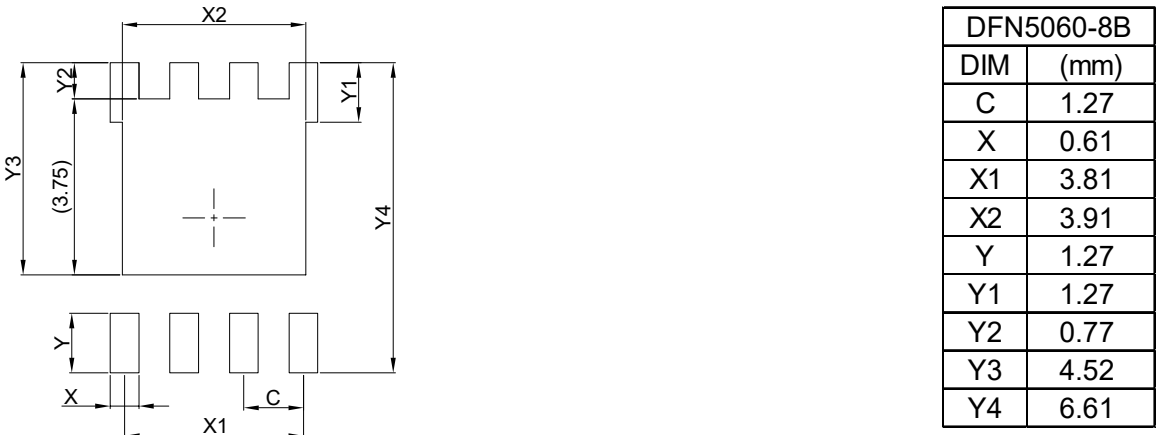


8.OUTLINE AND DIMENSIONS

DFN5060-8B



9.SOLDERING FOOTPRINT



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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